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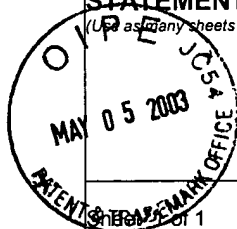
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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)



Complete if Known

Application Number	10/054601
Filing Date	January 22, 2002
First Named Inventor	Forbes, Leonard
Group Art Unit	2879
Examiner Name	Santiago, Mariceli

Attorney Docket No: 303.504US3

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Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date if Appropriate
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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EXAMINER

Mariceli Santiago

DATE CONSIDERED

7/3/03

Substitute Disclosure Statement Form (PTO-1449)

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Sheet 1 of 2

Form 1449*	Atty. Docket No.: 303.504US3	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: Herewith	Group: Unknown

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10/05/01
01/22/02

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**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No
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Examiner <i>Joseph Williams</i>	Date Considered <i>9/7/02</i>
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Sheet 2 of 2

Form 1449*	Atty. Docket No.: 303.504US3	Serial No. Unknown 10/054601
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: Herewith	Group: Unknown 2879

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Examiner <i>Joseph Williams fu</i>	Date Considered <i>9/7/02</i>
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